

GSS1N5400 Series

Axial Lead Silicon Rectifiers

Product Description

Silicon Rectifiers 3.0A / 50V To 1000V

Features

- Low Forward Voltage Drop
- High Current Capacity
- High Reliability
- High Surge Current Capability
- Lead(Pb)-Free

Mechanical Data

- Case : Molded Plastic
- Epoxy : UL 94V-0 rate flame retardant
- Lead : Axial leads, solderable per MIL-STD-202, method 208 guaranteed
- Polarity : Color band denotes cathode end
- Mounting position : Any
- Weight : 1.10 grams

Packages



DO-201AD

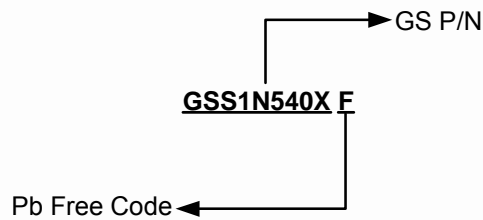
Marking Information

Part Number	Package	Marking
GSS1N5400F	DO-201AD	WTYYWW 1N5400.
GSS1N5401F	DO-201AD	WTYYWW 1N5401.
GSS1N5402F	DO-201AD	WTYYWW 1N5402.
GSS1N5404F	DO-201AD	WTYYWW 1N5404.
GSS1N5406F	DO-201AD	WTYYWW 1N5406.
GSS1N5407F	DO-201AD	WTYYWW 1N5407.
GSS1N5408F	DO-201AD	WTYYWW 1N5408.

※ "WT" GS Code & "YYWW" Date Code

※ "1N540X" GS P/N & "." Halogen Free

Ordering Information



Part Number	Package	Quantity
GSS1N5400F Series	DO-201AD	5000 PCS

Electrical Characteristics

Rating 25°C Ambient Temperature Unless Otherwise Specified.
 Single Phase Half Wave, 60Hz, Resistive or Inductive Load.
 For Capacitive Load, Derate Current by 20%.

Symbol	Conditions	1N5400	1N5401	1N5402	1N5404	Unit
V _{RRM}	Maximum Recurrent Peak Reverse Voltage	50	100	200	400	V
V _{RWS}	Maximum RMS Voltage	35	70	140	280	V
V _{DC}	Maximum DC Blocking Voltage	50	100	200	400	V
Symbol	Conditions	1N5406	1N5407	1N5408	Unit	
V _{RRM}	Maximum Recurrent Peak Reverse Voltage	600	800	1000	V	
V _{RWS}	Maximum RMS Voltage	420	560	700	V	
V _{DC}	Maximum DC Blocking Voltage	600	800	1000	V	
V _F	Maximum Instantaneous At 3.0A DC	1.1			V	
I _R	Maximum DC Reverse Current At Rated DC Blocking Voltage	T _A =25°C	5.0		uA	
		T _A =100°C	50			
C _J	Typical Junction Capacitance	40			pF	
I _{F(AV)}	Maximum Average Forward Rectified Current .375"(9.5mm) lead Length at T _A =75°C	3.0			A	
I _{FSM}	Peak Forward Surge Current, 8.3 ms Single Half Sine-Wave Superimposed on Rated Load	200			A	
R _{ΘJA}	Typical Thermal Resistance (2)	30			°C/W	
T _J	Junction Temperature Range	+175			°C	
T _{STG}	Storage Temperature Range	-65 to +170			°C	

Notes: 1. Measured at 1.0MHz applied reverse voltage of 4.0V DC
 2. Thermal Resistance Junction to case

Typical Characteristics

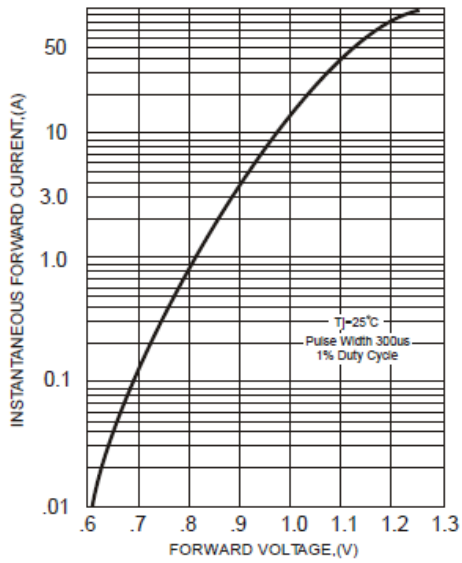


FIG. 1-TYPICAL FORWARD CHARACTERISTICS

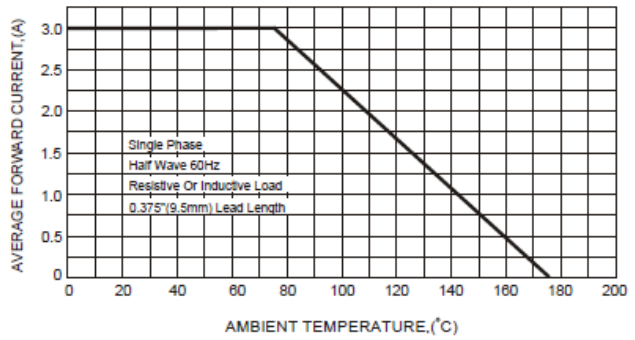


FIG. 2-TYPICAL FORWARD CURRENT DERATING CURVE

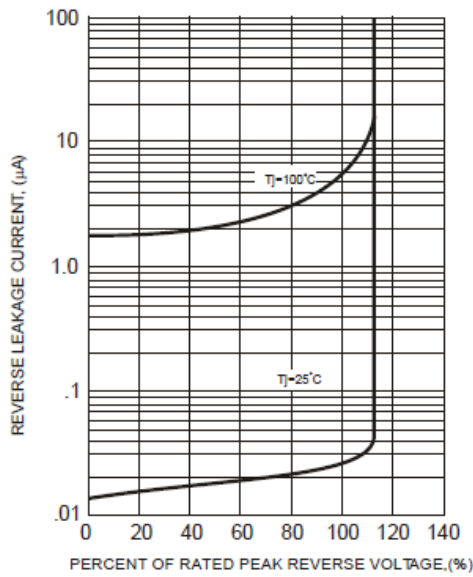


FIG. 3 - TYPICAL REVERSE CHARACTERISTICS

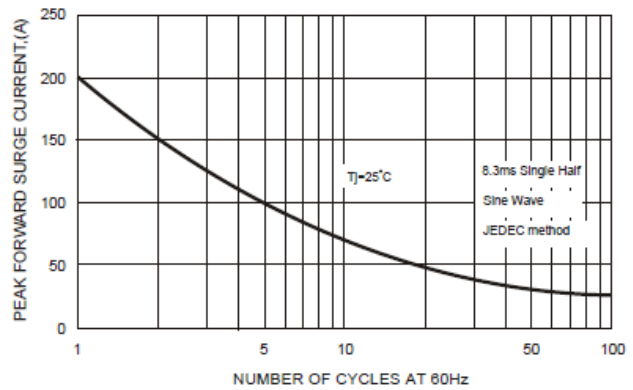


FIG. 4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

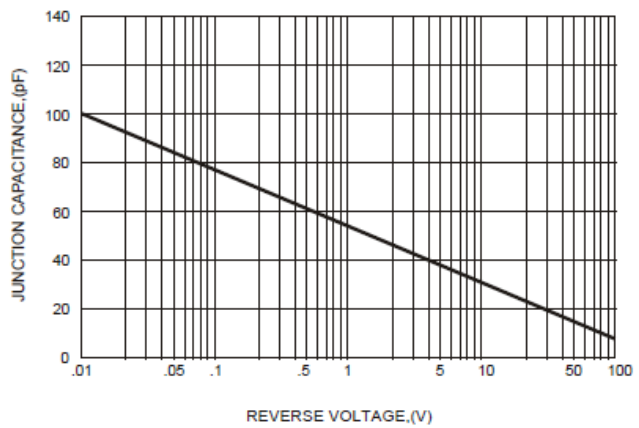
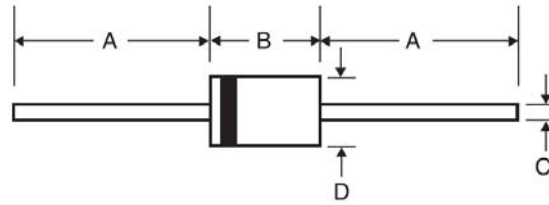


FIG. 5-TYPICAL JUNCTION CAPACITANCE

Package Dimension

DO-201AD











Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	25.40	-	1.000	-
B	7.30	9.50	0.287	0.374
C	1.20	1.30	0.047	0.051
D	4.80	5.60	0.188	0.220



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CONTACT US

GS Headquarter	
	4F.,No.43-1,Lane11,Sec.6,Minquan E.Rd Neihu District Taipei City 114, Taiwan (R.O.C)
	886-2-2657-9980
	886-2-2657-3630
	sales_twn@gs-power.com

Wu-Xi Branch	
	No.21 Changjiang Rd., WND, Wuxi, Jiangsu, China (INFO. & TECH. Science Park Building A 210 Room)
	86-510-85217051
	86-510-85211238
	sales_cn@gs-power.com

RD Division	
	824 Bolton Drive Milpitas. CA. 95035
	1-408-457-0587